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Chapter 1

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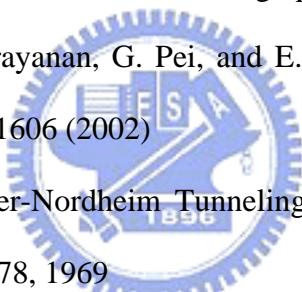
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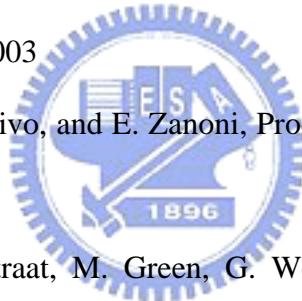
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chapter 4

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論文題目：

鍺鎬合金非揮發性記憶體之製作及研究

**Fabrication and study on $Zr_{1-x}Ge_x$ for nonvolatile
memory device**